

Notice of References Cited		Application/Control No.	Applicant(s)/Patent Under Reexamination OHTO ET AL.	
		Examiner Jarrett J. Stark	Art Unit 2823	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-2003/0235710	12-2003	Grill et al.	428/641
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
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	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Jiang L.; Chen X.; Wang X.; Xu L.1; Stubhan F.; Merkel K.-H. a-SiCx:H films deposited by plasma-enhanced chemical vapor deposition at low temperature used for moisture and corrosion resistant applications, Thin Solid Films, Volume 352, Number 1, 8 September 1999, pp. 97-101(5)
	V	A. M. Wróbel, I. Baszczyk, A. Walkiewicz-Pietrzykowska, ; Remote hydrogen–nitrogen plasma chemical vapor deposition from a tetramethyldisilazane source. Part 1. Mechanism of the process, structure and surface morphology of deposited amorphous hydrogenated silicon carbonitride films, Journal of Materials Chemistry, 2003, 13, 731 - 737
	W	Mark A. Petrich, Karen K. Gleason, and Jeffrey A. Reimer; Structure and properties of amorphous hydrogenated silicon carbide, Phys. Rev. B 36, 9722–9731 (1987)
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.